

74HC2G66; 74HCT2G66

Dual single-pole single-throw analog switch

Rev. 06 — 2 April 2010

Product data sheet

1. General description

74HC2G66 and 74HCT2G66 are high-speed Si-gate CMOS devices. They are dual single-pole single-throw analog switches. Each switch has two input/output pins (nY and nZ) and an active HIGH enable input pin (nE). When pin nE is LOW, the analog switch is turned off.

2. Features and benefits

- Wide supply voltage range from 2.0 V to 10.0 V for 74HC2G66
- Very low ON resistance:
 - ◆ 41 Ω (typ.) at $V_{CC} = 4.5$ V
 - ◆ 30 Ω (typ.) at $V_{CC} = 6.0$ V
 - ◆ 21 Ω (typ.) at $V_{CC} = 9.0$ V
- High noise immunity
- Low power dissipation
- 25 mA continuous switch current
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G66DP 74HCT2G66DP	-40 °C to $+125$ °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC2G66DC 74HCT2G66DC	-40 °C to $+125$ °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC2G66GD 74HCT2G66GD	-40 °C to $+125$ °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLT based; body $3 \times 2 \times 0.5$ mm	SOT996-2

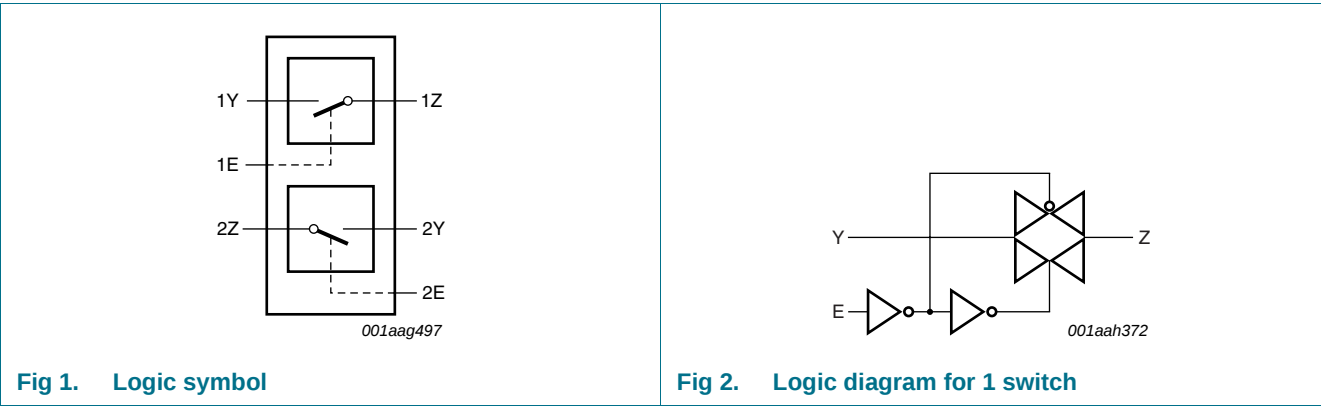


4. Marking

Table 2. Marking codes

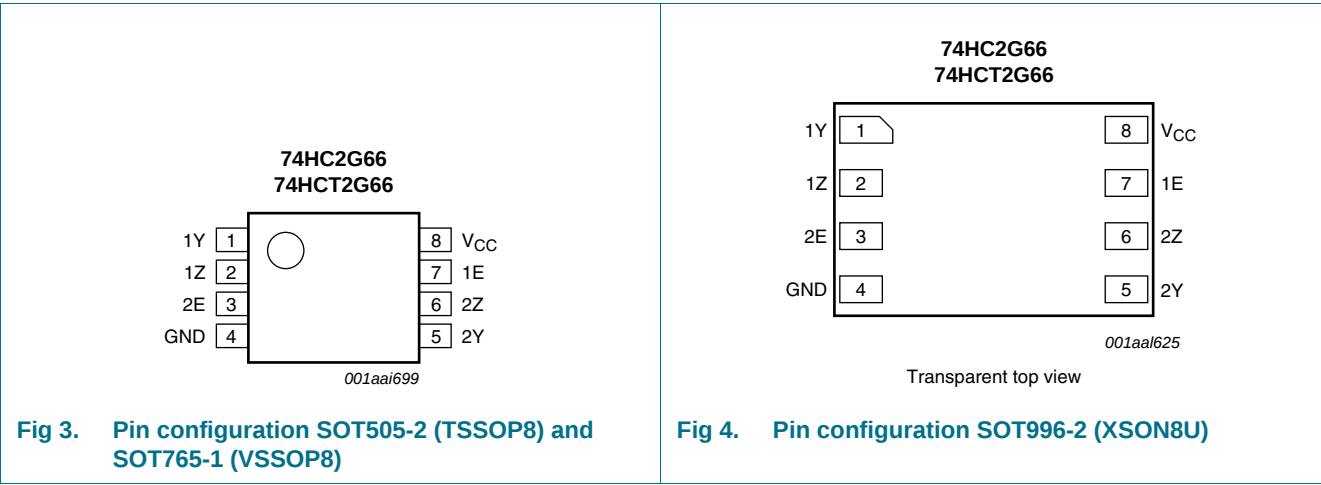
Type number	Marking
74HC2G66DP	H66
74HCT2G66DP	T66
74HC2G66DC	H66
74HCT2G66DC	T66
74HC2G66GD	H66
74HCT2G66GD	T66

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1Y, 2Y	1, 5	independent input or output
1Z, 2Z	2, 6	independent input or output
GND	4	ground (0 V)
1E, 2E	7, 3	enable input (active HIGH)
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input nE	Switch
L	OFF
H	ON

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+11.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{SK}	switch clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{SW}	switch current	V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V	-	±20	mA
I _{CC}	supply current		-	30	mA
I _{GND}	ground current		-30	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
		per package	^[2] -	300	mW
		per switch	^[2] -	100	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 packages above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 packages above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.
 For XSON8U package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).^[1]

Symbol	Parameter	Conditions	74HC2G66			74HCT2G66			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	10.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _{SW}	switch voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V
		V _{CC} = 10.0 V	-	-	35	-	-	-	ns/V

- [1] To avoid drawing V_{CC} current out of pin nZ, when switch current flows in pin nY, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into pin nZ, no V_{CC} current will flow out of terminal nY. In this case there is no limit for the voltage drop across the switch, but the voltage at pins nY and nZ may not exceed V_{CC} or GND.

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

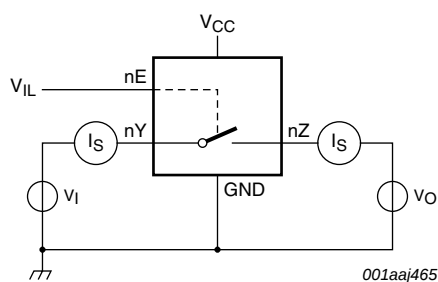
Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
74HC2G66								
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
		V _{CC} = 9.0 V	6.3	4.7	-	6.3	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
		V _{CC} = 9.0 V	-	4.3	2.7	-	2.7	V
I _I	input leakage current	nE; V _I = V _{CC} or GND						
		V _{CC} = 6.0 V	-	-	±0.1	-	±0.1	μA
		V _{CC} = 9.0 V	-	-	±0.2	-	±0.2	μA
I _{S(OFF)}	OFF-state leakage current	nY or nZ; V _{CC} = 9.0 V; see Figure 5	-	0.1	1.0	-	1.0	μA
I _{S(ON)}	ON-state leakage current	nY or nZ; V _{CC} = 9.0 V; see Figure 6	-	0.1	1.0	-	1.0	μA
I _{CC}	supply current	nE, nY and nZ = V _{CC} or GND						
		V _{CC} = 6.0 V	-	-	10	-	20	μA
		V _{CC} = 9.0 V	-	-	20	-	40	μA

Table 7. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
C_I	input capacitance		-	3.5	-	-	-	pF
C_{PD}	power dissipation capacitance		-	9	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance		-	8	-	-	-	pF
74HCT2G66								
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	V
I_I	input leakage current	nE; $V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	± 1.0	-	± 1.0	μA
$I_{S(OFF)}$	OFF-state leakage current	nY or nZ; $V_{CC} = 5.5\text{ V}$; see Figure 5	-	0.1	1.0	-	1.0	μA
$I_{S(ON)}$	ON-state leakage current	nY or nZ; $V_{CC} = 5.5\text{ V}$; see Figure 6	-	0.1	1.0	-	1.0	μA
I_{CC}	supply current	nE, nY and nZ = V_{CC} or GND; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	nE = $V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$;	-	-	375	-	410	μA
C_I	input capacitance		-	3.5	-	-	-	pF
C_{PD}	power dissipation capacitance		-	9	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance		-	8	-	-	-	pF

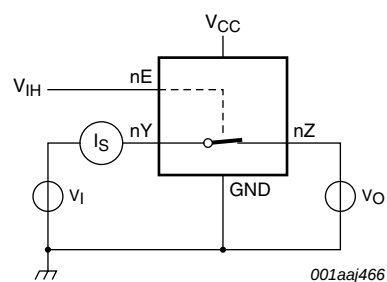
[1] Typical values are measured at $T_{amb} = 25\text{ °C}$.

10.1 Test circuits



$V_I = V_{CC}$ or GND and $V_O = \text{GND or } V_{CC}$.

Fig 5. Test circuit for measuring OFF-state leakage current



$V_I = V_{CC}$ or GND and $V_O = \text{open circuit}$.

Fig 6. Test circuit for measuring ON-state leakage current

10.2 ON resistance

Table 8. ON resistance for 74HC2G66 and 74HCT2G66

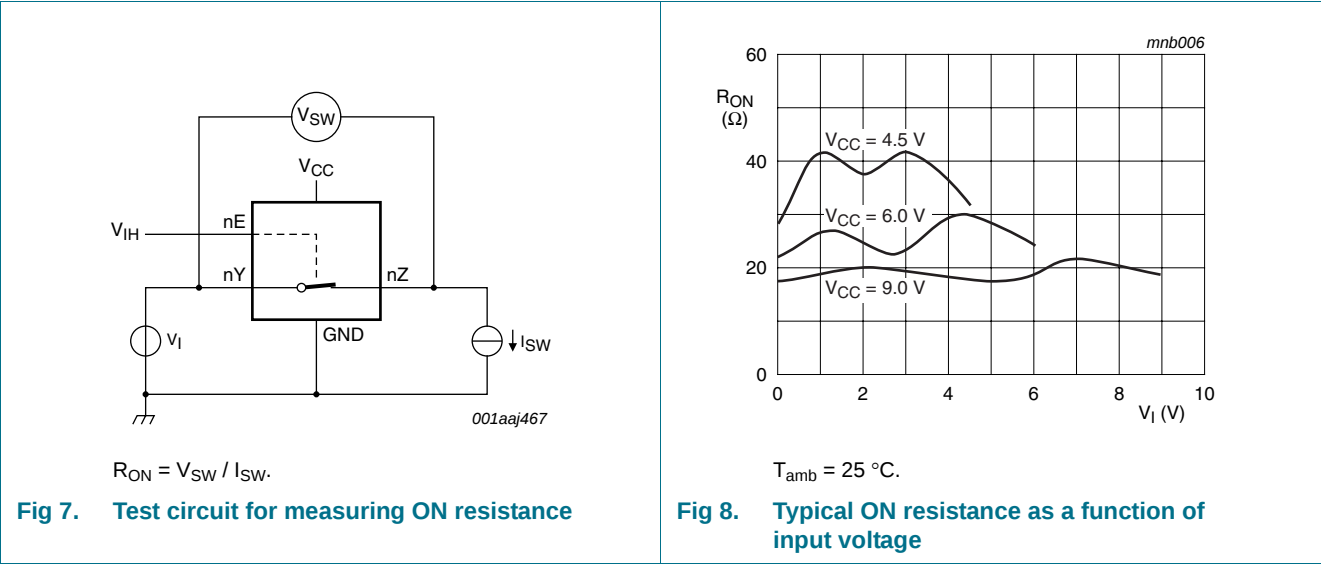
At recommended operating conditions; voltages are referenced to GND (ground 0 V); for graph see [Figure 8](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[2]	Max	Min	Max	
74HC2G66 ^[1]								
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; see Figure 7 and 8						
		I _{SW} = 0.1 mA; V _{CC} = 2.0 V	-	250	-	-	-	Ω
		I _{SW} = 1.0 mA; V _{CC} = 4.5 V	-	41	118	-	142	Ω
		I _{SW} = 1.0 mA; V _{CC} = 6.0 V	-	30	105	-	126	Ω
		I _{SW} = 1.0 mA; V _{CC} = 9.0 V	-	21	88	-	105	Ω
R _{ON(rail)}	ON resistance (rail)	V _I = GND; see Figure 7 and 8						
		I _{SW} = 0.1 mA; V _{CC} = 2.0 V	-	65	-	-	-	Ω
		I _{SW} = 1.0 mA; V _{CC} = 4.5 V	-	28	95	-	115	Ω
		I _{SW} = 1.0 mA; V _{CC} = 6.0 V	-	22	82	-	100	Ω
		I _{SW} = 1.0 mA; V _{CC} = 9.0 V	-	18	70	-	80	Ω
		V _I = V _{CC} ; see Figure 7 and 8						
		I _{SW} = 0.1 mA; V _{CC} = 2.0 V	-	65	-	-	-	Ω
		I _{SW} = 1.0 mA; V _{CC} = 4.5 V	-	31	106	-	128	Ω
		I _{SW} = 1.0 mA; V _{CC} = 6.0 V	-	23	94	-	113	Ω
		I _{SW} = 1.0 mA; V _{CC} = 9.0 V	-	19	78	-	95	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = V _{CC} to GND; see Figure 7 and 8						
		V _{CC} = 4.5 V	-	5	-	-	-	Ω
		V _{CC} = 6.0 V	-	4	-	-	-	Ω
		V _{CC} = 9.0 V	-	3	-	-	-	Ω
74HCT2G66								
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; see Figure 7 and 8						
		I _{SW} = 1.0 mA; V _{CC} = 4.5 V	-	41	118	-	142	Ω
R _{ON(rail)}	ON resistance (rail)	V _I = GND; see Figure 7 and 8						
		I _{SW} = 1.0 mA; V _{CC} = 4.5 V	-	28	95	-	115	Ω
		V _I = V _{CC} ; see Figure 7 and 8						
		I _{SW} = 1.0 mA; V _{CC} = 4.5 V	-	31	106	-	128	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = V _{CC} to GND; see Figure 7 and 8						
		V _{CC} = 4.5 V	-	5	-	-	-	Ω

[1] At supply voltages approaching 2 V, the ON resistance becomes extremely non-linear. Therefore it is recommended that these devices be used to transmit digital signals only, when using this supply voltage.

[2] Typical values are measured at T_{amb} = 25 °C.

10.3 ON resistance test circuit and graphs



11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
74HC2G66								
t _{pd}	propagation delay	nY to nZ or nZ to nY; R _L = ∞ Ω; see Figure 9	[2]					
		V _{CC} = 2.0 V	-	6.5	65	-	80	ns
		V _{CC} = 4.5 V	-	2	13	-	15	ns
		V _{CC} = 6.0 V	-	1.5	11	-	14	ns
		V _{CC} = 9.0 V	-	1.2	10	-	12	ns
t _{en}	enable time	nE to nY or nZ; see Figure 10	[2]					
		V _{CC} = 2.0 V	-	40	125	-	150	ns
		V _{CC} = 4.5 V	-	12	29	-	30	ns
		V _{CC} = 6.0 V	-	10	21	-	26	ns
		V _{CC} = 9.0 V	-	7	16	-	20	ns
t _{dis}	disable time	nE to nY or nZ; see Figure 10	[2]					
		V _{CC} = 2.0 V	-	21	145	-	175	ns
		V _{CC} = 4.5 V	-	12	29	-	35	ns
		V _{CC} = 6.0 V	-	11	28	-	33	ns
		V _{CC} = 9.0 V	-	10	23	-	27	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC}	[3]	-	9	-	-	pF

Table 9. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); For test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
74HCT2G66								
t _{pd}	propagation delay	nY to nZ or nZ to nY; R _L = ∞ Ω; see Figure 9	[2]					
		V _{CC} = 4.5 V	-	2	15	-	18	ns
t _{en}	enable time	nE to nY or nZ; see Figure 10	[2]					
		V _{CC} = 4.5 V	-	13	30	-	36	ns
t _{dis}	disable time	nE to nY or nZ; see Figure 10	[2]					
		V _{CC} = 4.5 V	-	13	44	-	53	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} − 1.5 V	[3]	-	9	-	-	pF

[1] All typical values are measured at $T_{amb} = 25 \text{ °C}$.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

t_{en} is the same as t_{PZL} and t_{PZH} .

t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[3] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma((C_L \times C_{SW}) \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

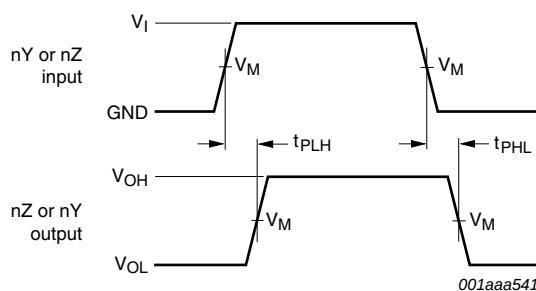
C_L = output load capacitance in pF;

C_{SW} = maximum switch capacitance in pF (see [Table 7](#));

V_{CC} = supply voltage in volts;

$\Sigma((C_L \times C_{SW}) \times V_{CC}^2 \times f_o)$ = sum of outputs.

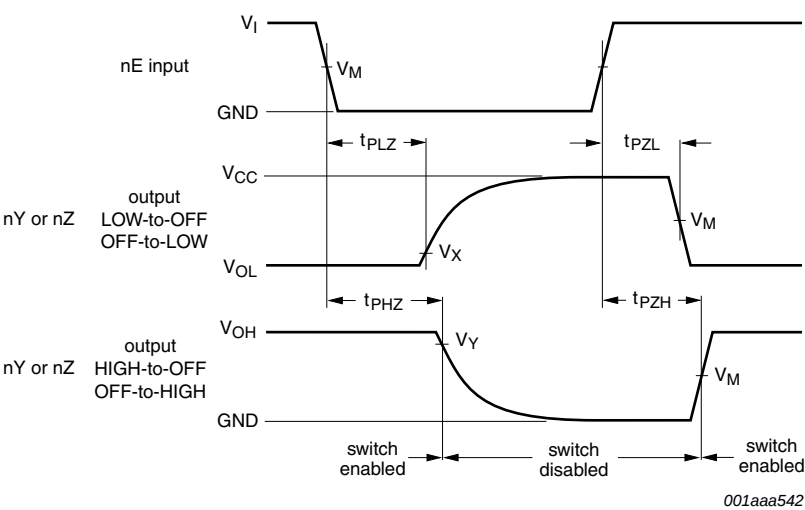
11.1 Waveforms and test circuit



Measurement points are given in [Table 10](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 9. Input (nY or nZ) to output (nZ or nY) propagation delays

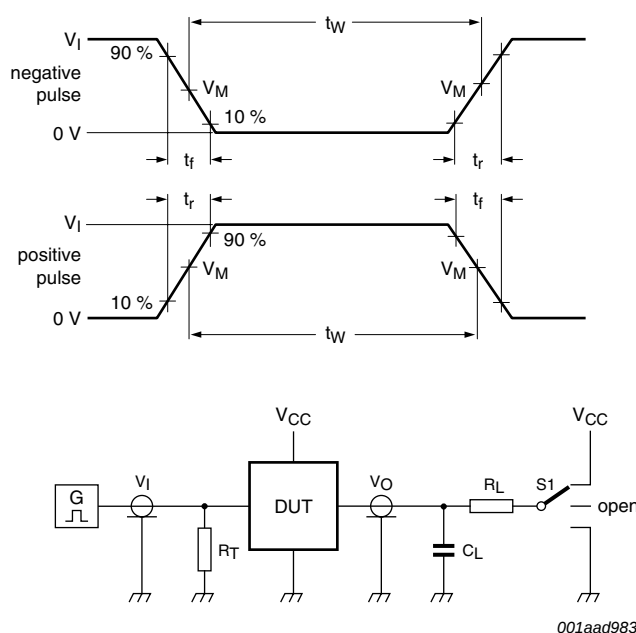


Measurement points are given in [Table 10](#).
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 10. Enable and disable times

Table 10. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC2G66	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 10\%$	$V_{OH} - 10\%$
74HCT2G66	1.3 V	1.3 V	$V_{OL} + 10\%$	$V_{OH} - 10\%$



Test data is given in [Table 11](#).

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 11. Test circuit for measuring switching times

Table 11. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f ^[1]	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC2G66	GND to V_{CC}	6 ns	50 pF	1 k Ω	open	GND	V_{CC}
74HCT2G66	GND to 3 V	6 ns	50 pF	1 k Ω	open	GND	V_{CC}

[1] There is no constraint on t_r, t_f with a 50 % duty factor when measuring f_{max} .

11.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics for 74HC2G66 and 74HCT2G66

$GND = 0 V$; $t_r = t_f = 6.0 ns$; $C_L = 50 pF$; unless otherwise specified. All typical values are measured at $T_{amb} = 25 ^\circ C$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
THD	total harmonic distortion	$f_i = 1 kHz$; $R_L = 10 k\Omega$; see Figure 12				%
		$V_{CC} = 4.5 V$; $V_I = 4.0 V$ (p-p)	-	0.04	-	%
		$V_{CC} = 9.0 V$; $V_I = 8.0 V$ (p-p)	-	0.02	-	%
		$f_i = 10 kHz$; $R_L = 10 k\Omega$; see Figure 12				
		$V_{CC} = 4.5 V$; $V_I = 4.0 V$ (p-p)	-	0.12	-	%
		$V_{CC} = 9.0 V$; $V_I = 8.0 V$ (p-p)	-	0.06	-	%

Table 12. Additional dynamic characteristics for 74HC2G66 and 74HCT2G66 ...continued

$GND = 0\text{ V}$; $t_r = t_f = 6.0\text{ ns}$; $C_L = 50\text{ pF}$; unless otherwise specified. All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{(-3\text{dB})}$	-3 dB frequency response	$R_L = 50\text{ }\Omega$; $C_L = 10\text{ pF}$; see Figure 13 and 14				
		$V_{CC} = 4.5\text{ V}$	-	180	-	MHz
		$V_{CC} = 9.0\text{ V}$	-	200	-	MHz
α_{iso}	isolation (OFF-state)	$R_L = 600\text{ }\Omega$; $f_i = 1\text{ MHz}$; see Figure 15 and 16				
		$V_{CC} = 4.5\text{ V}$	-	-50	-	dB
		$V_{CC} = 9.0\text{ V}$	-	-50	-	dB
V_{ct}	crosstalk voltage	between digital input and switch (peak to peak value); $R_L = 600\text{ }\Omega$; $f_i = 1\text{ MHz}$; see Figure 17				
		$V_{CC} = 4.5\text{ V}$	-	110	-	mV
		$V_{CC} = 9.0\text{ V}$	-	220	-	mV
Xtalk	crosstalk	between switches; $R_L = 600\text{ }\Omega$; $f_i = 1\text{ MHz}$; see Figure 18				
		$V_{CC} = 4.5\text{ V}$	-	-60	-	dB
		$V_{CC} = 9.0\text{ V}$	-	-60	-	dB

11.3 Test circuits and graphs

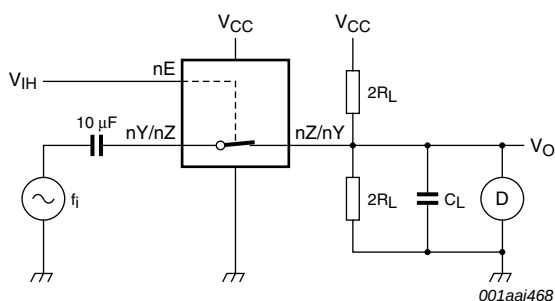
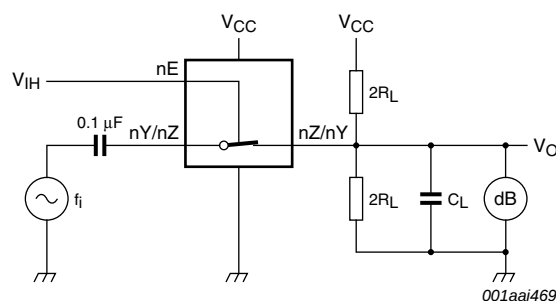
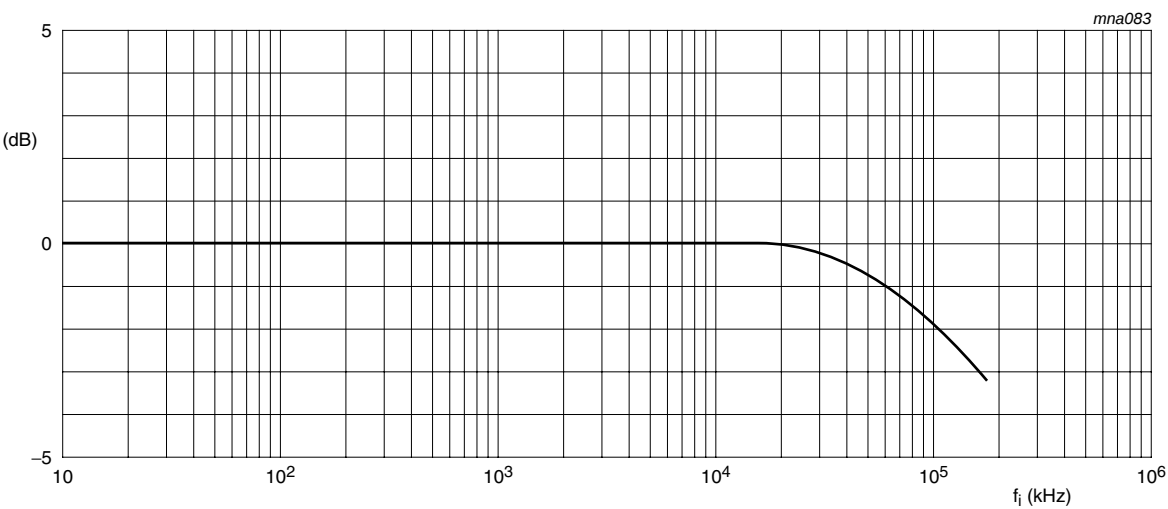


Fig 12. Test circuit for measuring total harmonic distortion



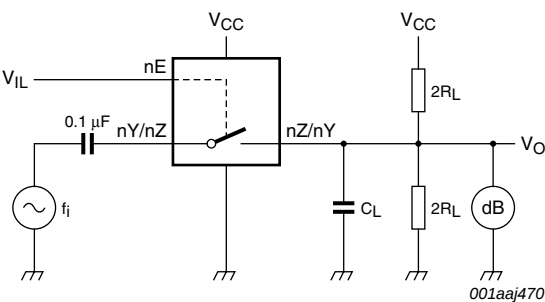
With $f_i = 1\text{ MHz}$ adjust the switch input voltage for a 0 dBm level at the switch output, (0 dBm = 1 mW into 50 Ω). Then increase the input frequency until the dB meter reads -3 dB.

Fig 13. Test circuit for measuring the -3 dB frequency response



Test conditions: $V_{CC} = 4.5\text{ V}$; $GND = 0\text{ V}$; $R_L = 50\text{ }\Omega$; $R_{SOURCE} = 1\text{ k}\Omega$.

Fig 14. Typical -3 dB frequency response



Adjust the switch input voltage for a 0 dBm level (0 dBm = 1 mW into 600 Ω)

Fig 15. Test circuit for measuring isolation (OFF-state)

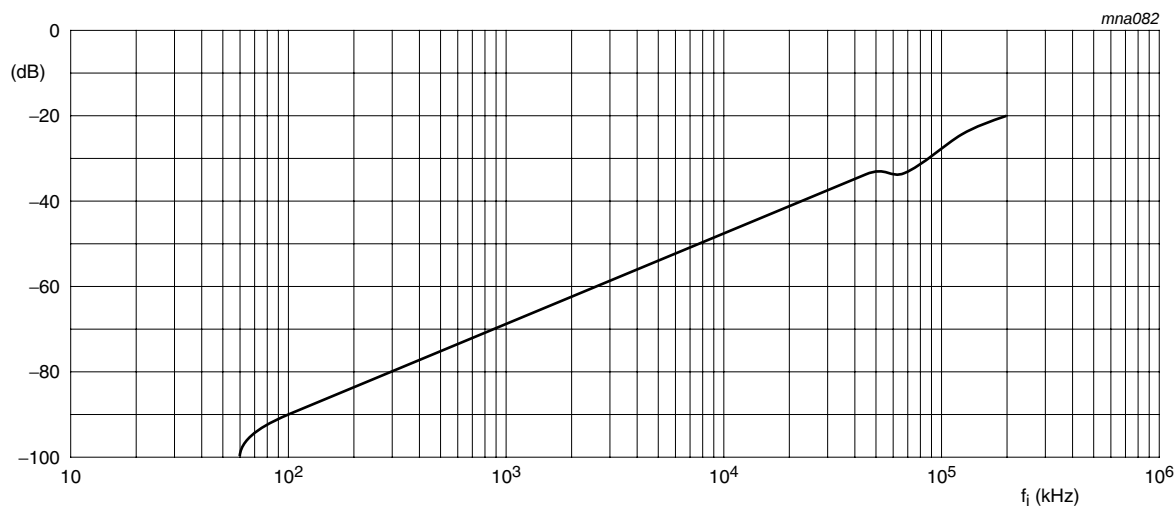
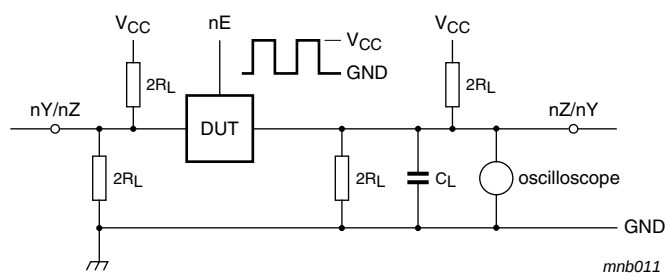
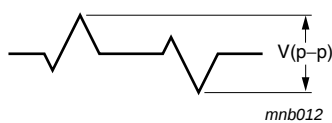


Fig 16. Typical isolation (OFF-state) as a function of frequency



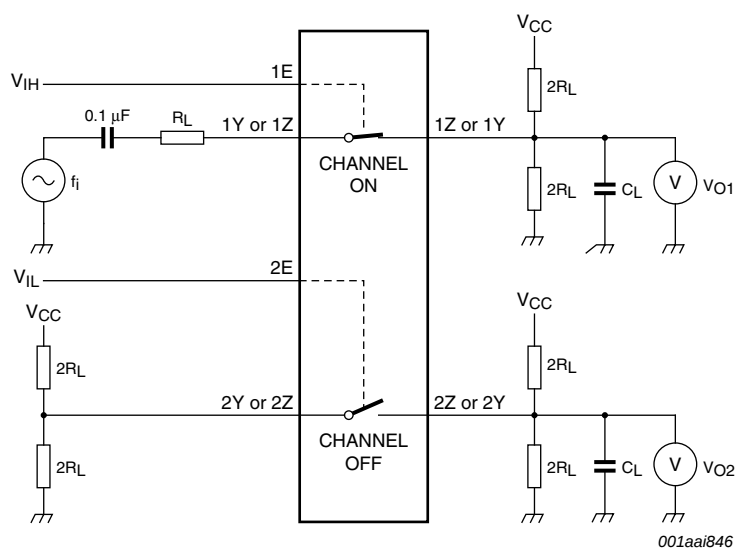
a. Circuit



b. Crosstalk voltage

Adjust the switch input voltage for a 0 dBm level (0 dBm = 1 mW into 600 Ω)

Fig 17. Test circuit for measuring crosstalk voltage (between the digital input and the switch)



Adjust the switch input voltage for a 0 dBm level (0 dBm = 1 mW into 600 Ω)

Fig 18. Test circuit for measuring crosstalk (between the switches)

12. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

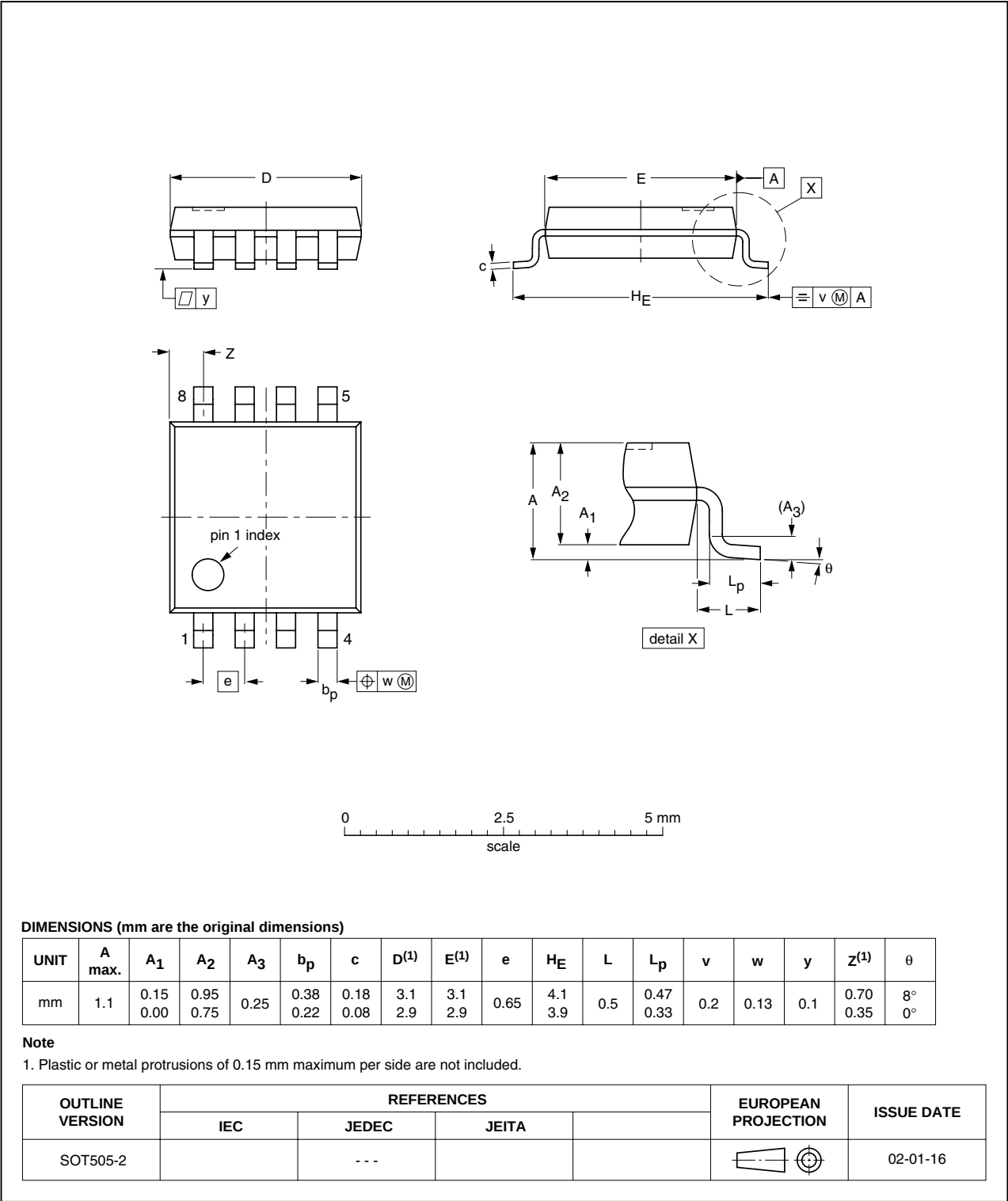


Fig 19. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

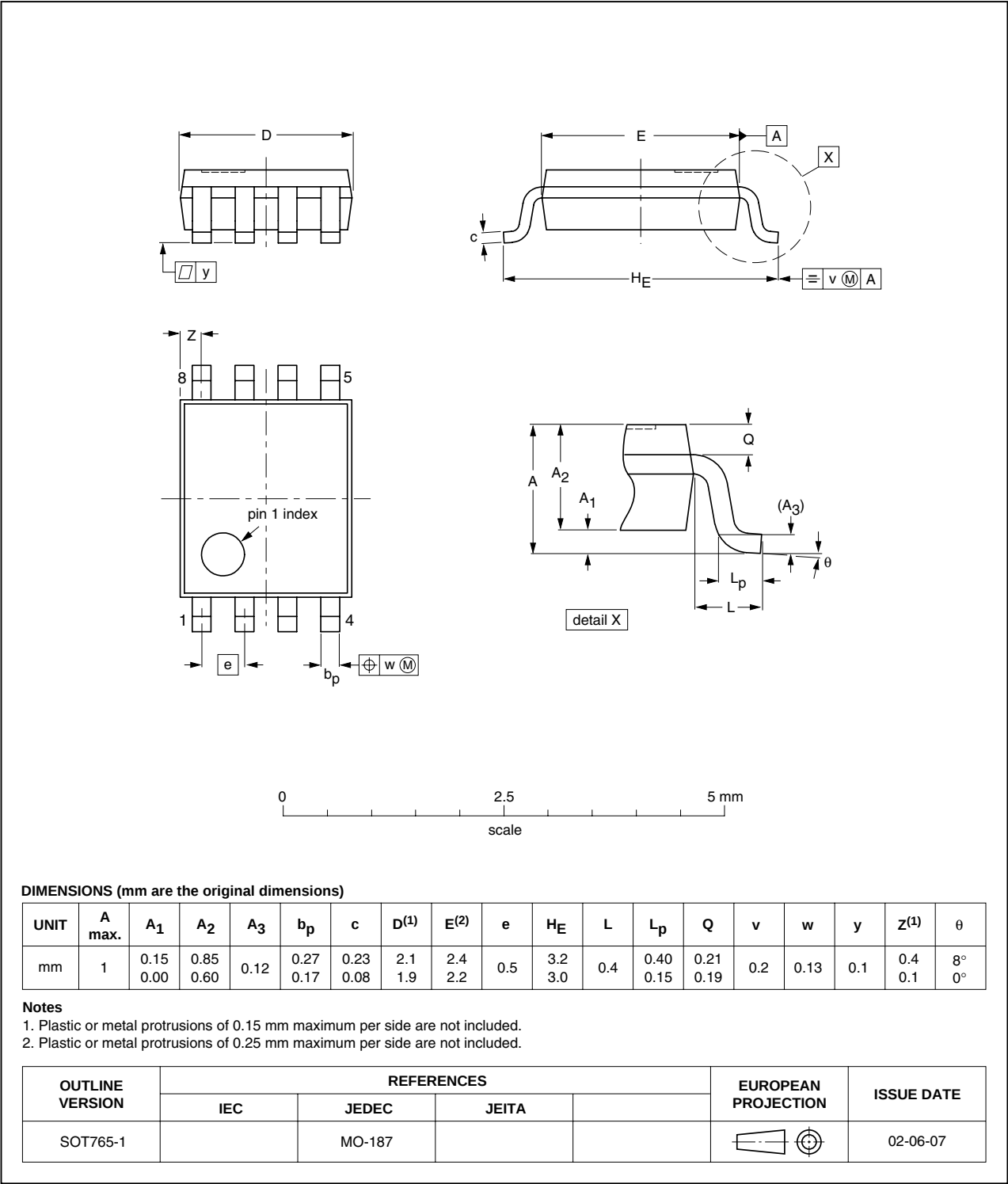


Fig 20. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

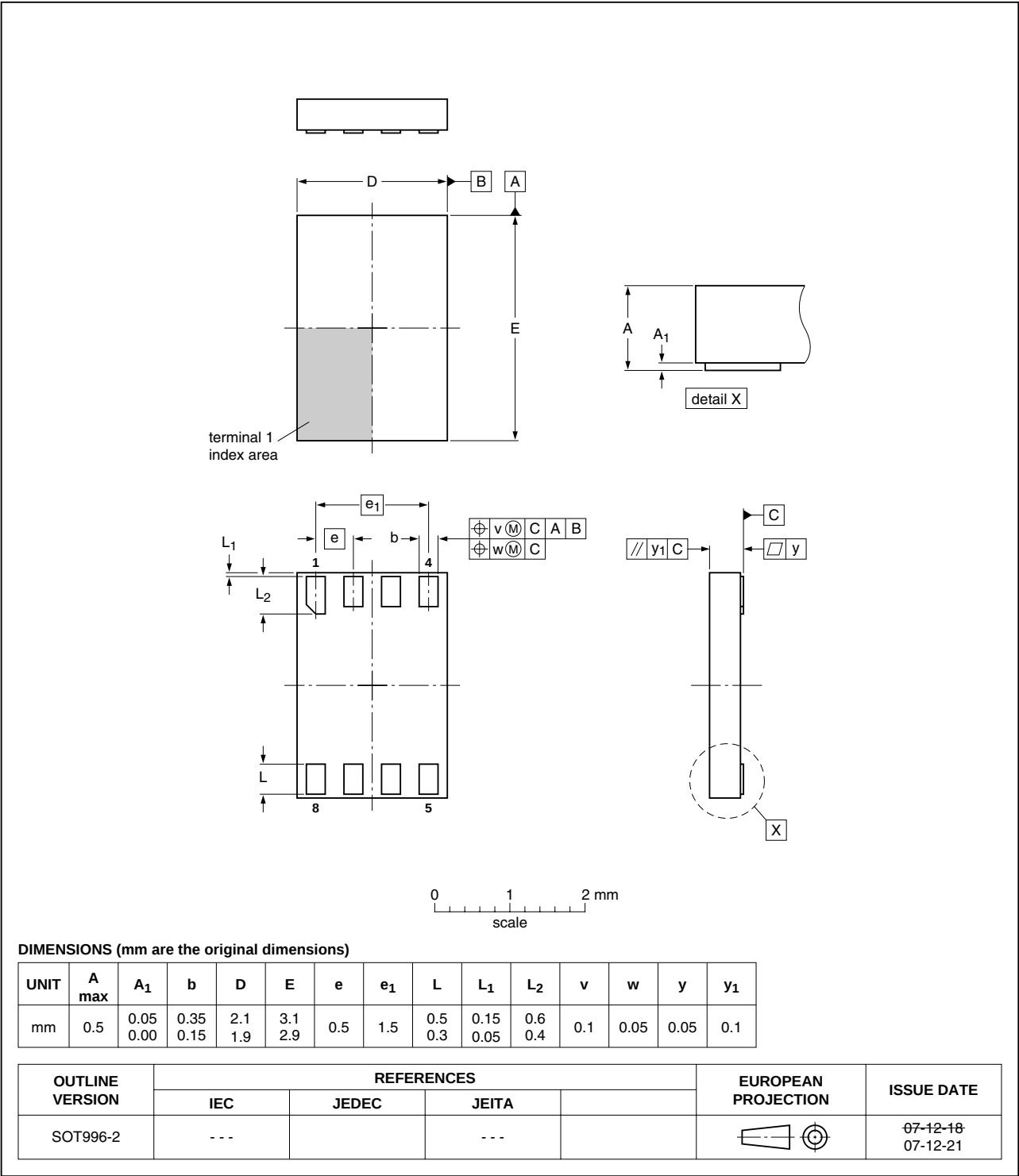


Fig 21. Package outline SOT996-2 (XSON8U)

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
DUT	Device Under Test

14. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G66_6	20100402	Product data sheet	-	74HC_HCT2G66_5
Modifications:	Added type number 74HC2G66GD and 74HCT2G66GD (XSON8U package)			
74HC_HCT2G66_5	20090126	Product data sheet	-	74HC_HCT2G66_4
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate. Table 1 "Ordering information" and Section 12 "Package outline" package SOT765-1 added. - Quick Reference Data and Soldering sections removed. Section 2 "Features and benefits" updated.			
74HC_HCT2G66_4	20040519	Product specification	-	74HC_HCT2G66_3
74HC_HCT2G66_3	20031126	Product specification	-	74HC_HCT2G66_2
74HC_HCT2G66_2	20030808	Product specification	-	74HC_HCT2G66_1
74HC_HCT2G66_1	20030625	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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